

Dual N-channel MOSFET

ELM51912EA-S

<http://www.elm-tech.com>

■ General description

ELM51912EA-S uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and operation with gate voltages as low as 1.8V and internal ESD protection.

■ Features

- $V_{ds}=20V$
- $I_d=1.4A$
- $R_{ds(on)} = 280m\Omega$ ($V_{gs}=4.5V$)
- $R_{ds(on)} = 340m\Omega$ ($V_{gs}=2.5V$)
- $R_{ds(on)} = 580m\Omega$ ($V_{gs}=1.8V$)
- ESD protected

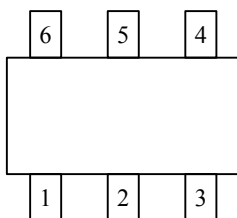
■ Maximum absolute ratings

$T_a=25^\circ C$. Unless otherwise noted.

Parameter	Symbol	Limit	Unit
Drain-source voltage	V_{ds}	20	V
Gate-source voltage	V_{gs}	± 12	V
Continuous drain current($T_j=150^\circ C$)	I_d	$T_a=25^\circ C$	1.4
		$T_a=70^\circ C$	1.0
Pulsed drain current	I_{dm}	6.0	A
Power dissipation	P_d	$T_c=25^\circ C$	0.3
		$T_c=70^\circ C$	0.2
Operating junction temperature	T_j	- 55 to 150	$^\circ C$
Storage temperature range	T_{stg}	- 55 to 150	$^\circ C$

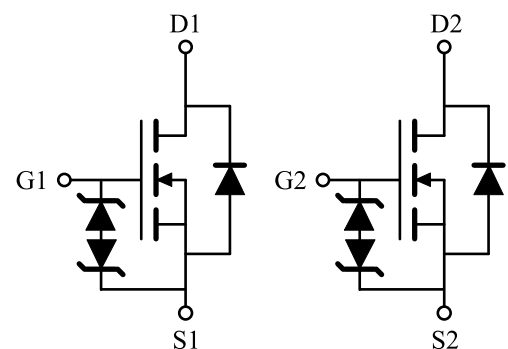
■ Pin configuration

SC-70-6(TOP VIEW)



Pin No.	Pin name
1	SOURCE1
2	GATE1
3	DRAIN2
4	SOURCE2
5	GATE2
6	DRAIN1

■ Circuit



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■ Electrical characteristics

Ta=25°C. Unless otherwise noted.

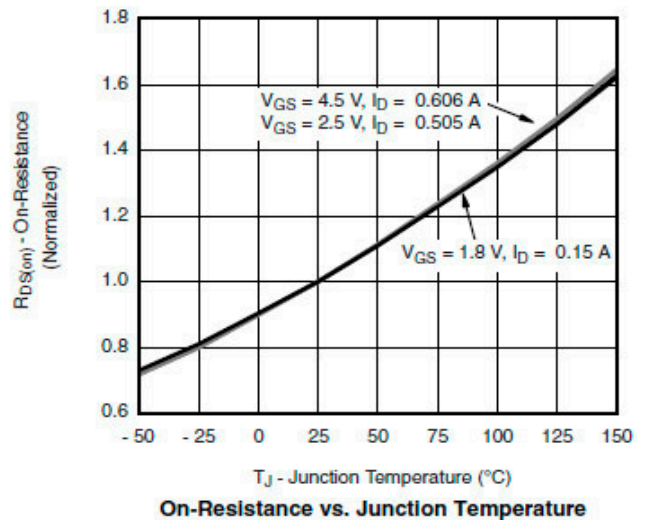
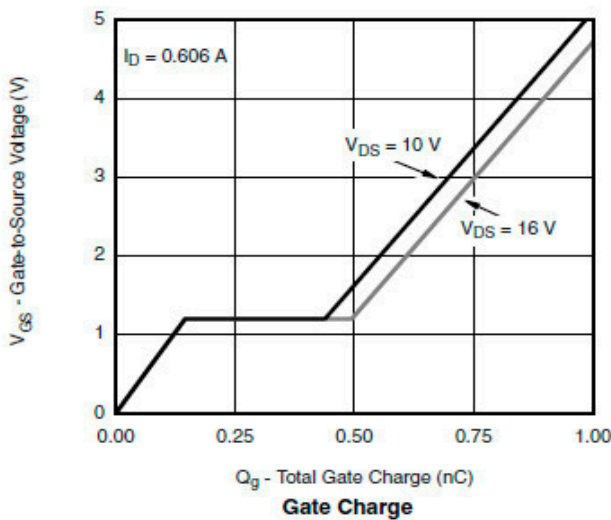
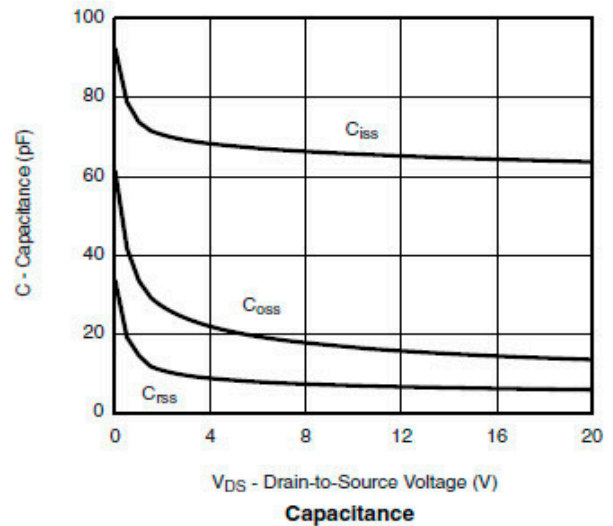
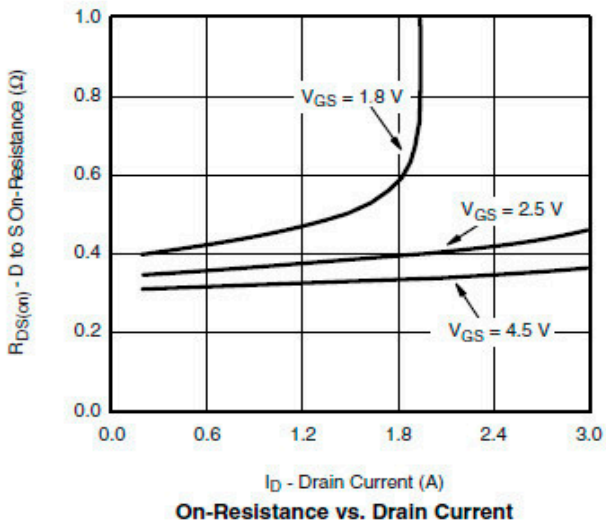
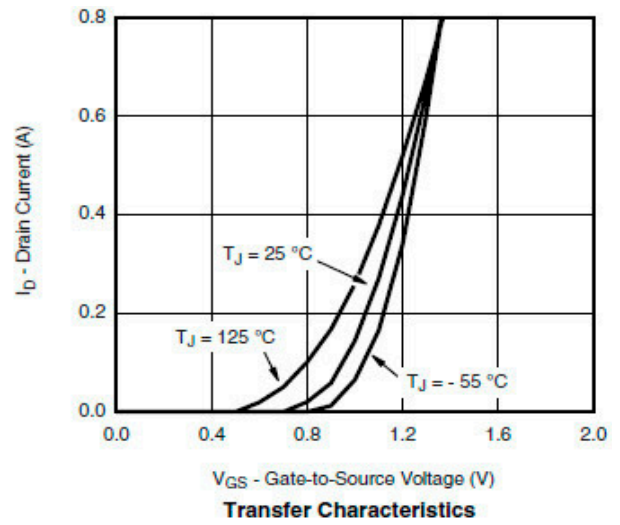
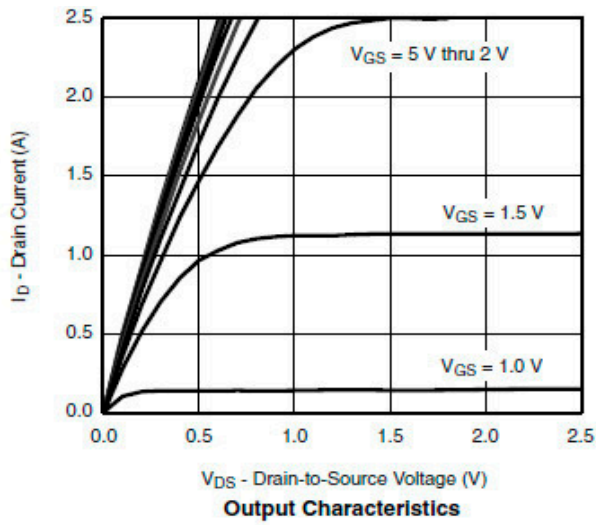
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	BVdss	Id=250μA, Vgs=0V	20			V
Zero gate voltage drain current	Idss	Vds=16V, Vgs=0V Ta=85°C			1	μA
					5	
Gate-source leakage current	Igss	Vds=0V, Vgs=±12V			±1	mA
Gate threshold voltage	Vgs(th)	Vds=Vgs, Id=250μA	0.3		0.8	V
On state drain current	Id(on)	Vgs=4.5V, Vds≥5V	1.4			A
Static drain-source on-resistance	Rds(on)	Vgs=4.5V, Id=1.8A		220	280	mΩ
		Vgs=2.5V, Id=1.5A		260	340	
		Vgs=1.8V, Id=1.2A		340	580	
Forward transconductance	Gfs	Vds=10V, Id=1.0A		1		S
Diode forward voltage	Vsd	Is=1.0A, Vgs=0V		0.65	1.20	V
Max. body-diode continuous current	Is				1.0	A
DYNAMIC PARAMETERS						
Input capacitance	Ciss	Vgs=0V, Vds=10V, f=1MHz		70		pF
Output capacitance	Coss			20		pF
Reverse transfer capacitance	Crss			8		pF
SWITCHING PARAMETERS						
Total gate charge	Qg	Vgs=4.5V, Vds=10V, Id=1.2A		1.06	1.38	nC
Gate-source charge	Qgs			0.18		nC
Gate-drain charge	Qgd			0.32		nC
Turn-on delay time	td(on)	Vgs=4.5V, Vds=10V RL=20Ω, Id=1.2A Rgen=1.0Ω		18	26	ns
Turn-on rise time	tr			20	28	ns
Turn-off delay time	td(off)			70	110	ns
Turn-off fall time	tf			25	40	ns

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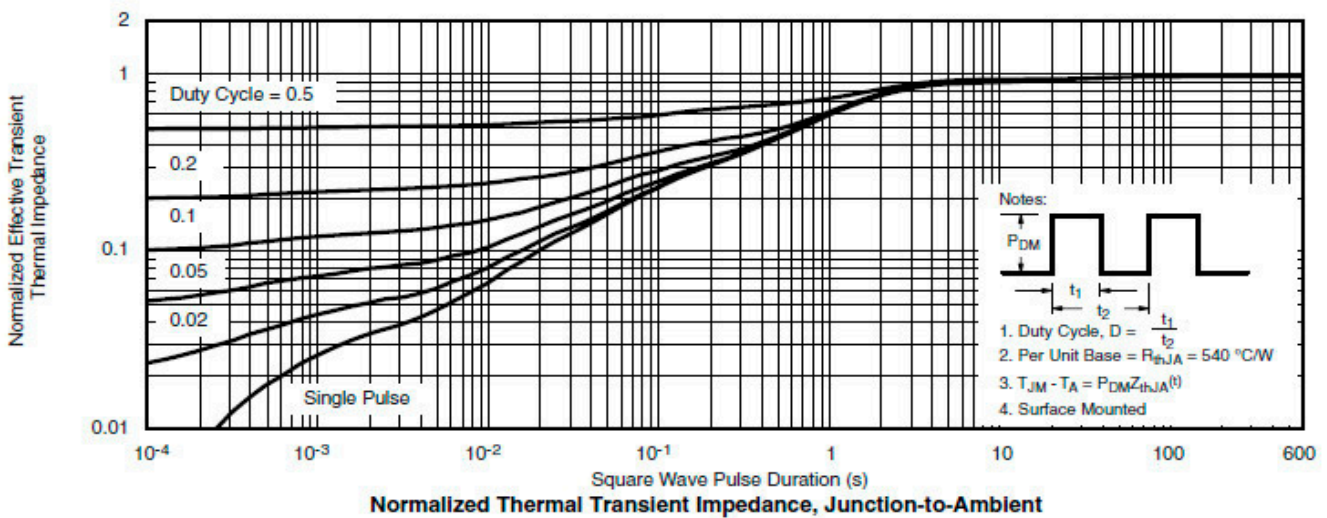
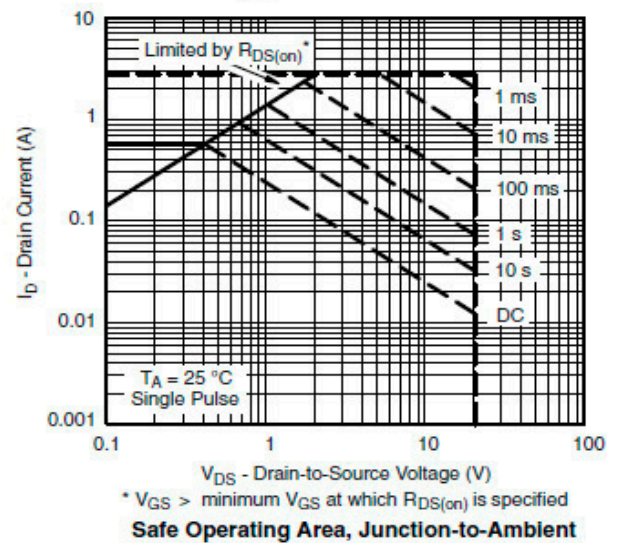
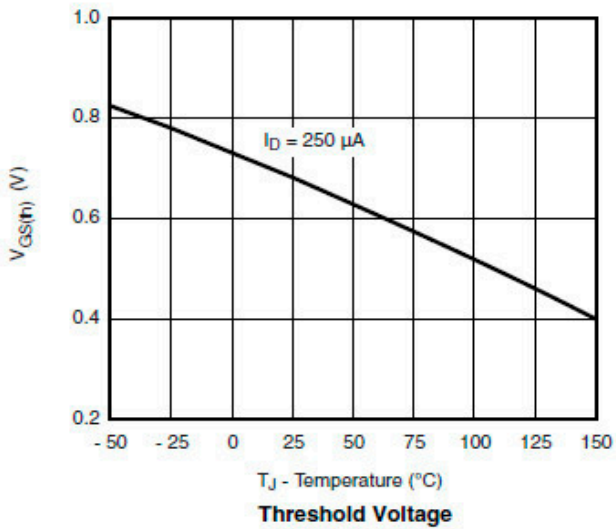
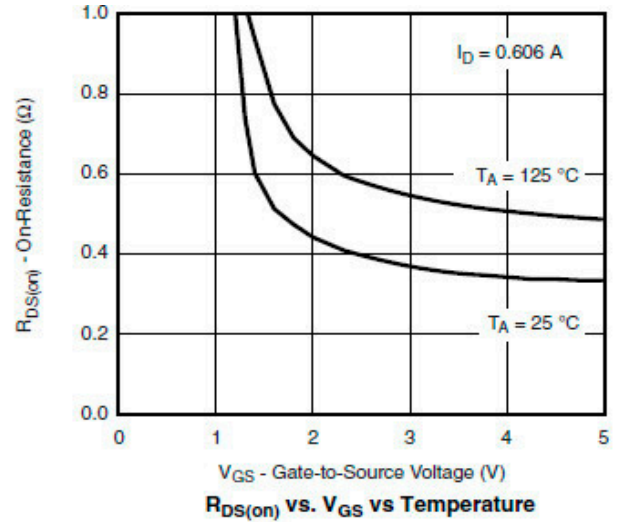
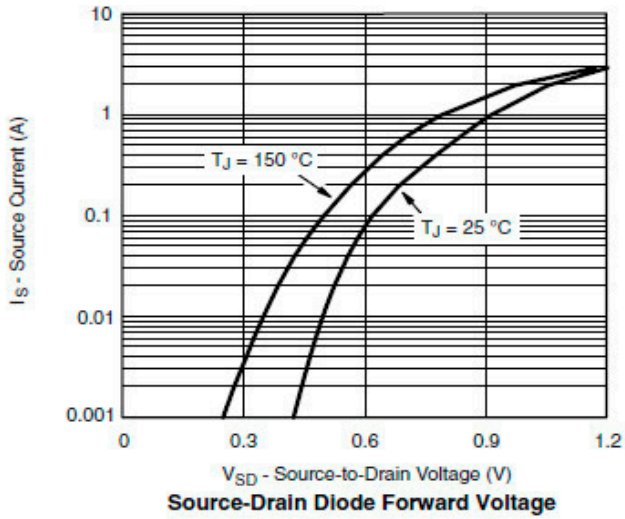
■ Typical electrical and thermal characteristics



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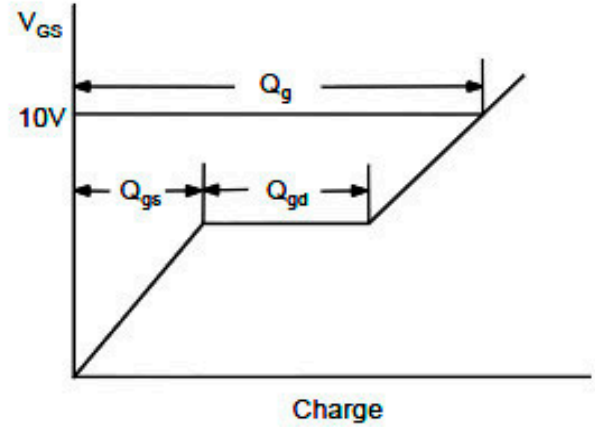
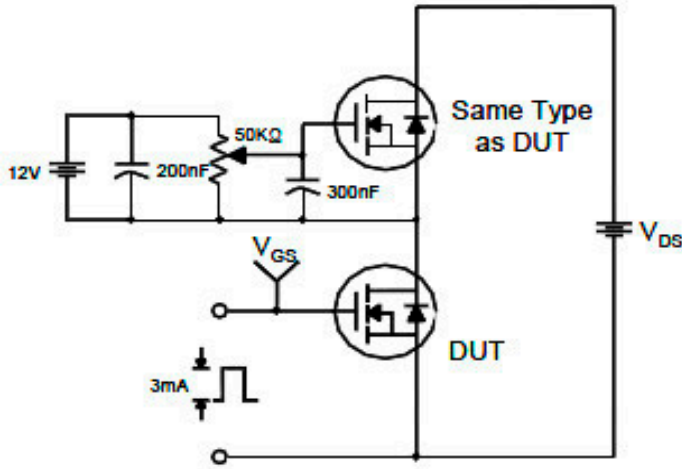
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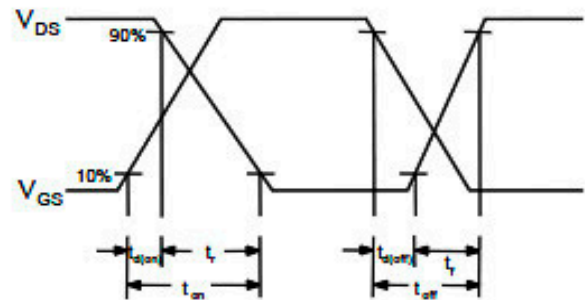
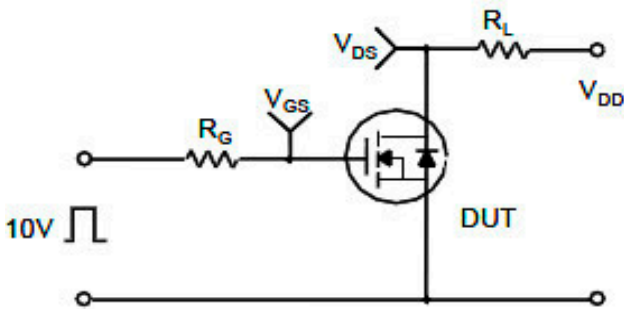
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■ Test circuit and waveform

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

